

The University of Manchester

Development and Simulation of 3D Diamond Detectors

Giulio Forcolin

ADAMAS Meeting

3 Dec 2015

Collaborators



University of Manchester



INFN Perugia





University of Oxford



Christie Hospital



RBI Zagreb



2

Introduction

- Manchester is working on the development of 3D Diamond Detectors
- Use laser to write graphitic wires into the Diamond bulk, possible to get features of size ~1µm (see talk by S. Murphy for details)
- Deposit metallization on samples to produce electrical contacts
- Detectors then tested and simulations used to try to understand behavior of carriers in diamond

Detector Manufacture

- Laser used to produce electrodes
- Use standard photolithographic process to produce patterned metallization on diamond



TCAD

- Used Sentaurus TCAD package for simulations
- Create a mesh to approximate the structure that needs to simulated
- Apply a set of boundary conditions (e.g. electrode potentials) to find the steady state behavior of the device
- Introduce a charge density in certain regions of the device to simulate e.g. a MIP hit or an α-particle
- Iteratively solving the governing equations of semiconductors, can therefore simulate behavior such as current pulses
- Can also add more advanced Physics
 models such as field dependent mobility



- TRIBIC (Time Resolved Ion Beam Induced Current)
 measurements on 3D Diamond sample
- 2013 Test beam in Zagreb, studied 3D Diamond detector with 4 MeV protons, and measured current produced
- 4MeV protons produce a Bragg peak ~80µm inside the diamond
- Self Triggered, ~ 2 μ m precision
- Simulate the shape of the current pulse generated





- Performed the simulations on a quarter square cell structure with 120µm pitch
- Approximated the deposited charge to a Bragg peak
- Running transient simulations to study the how the current pulse changes with different applied voltages and different hit positions



- Ran simulations at different voltages
- SC diamond, assume no traps; apply a resistance to the electrode
- Simulations included a surface metallization along the y direction to match the detector geometry used
- Applied bias voltage on the signal electrode, which was also read out; kept the HV electrode grounded



- Observed that with certain hit positions, particularly hits close to one of the electrodes, the current pulse exhibited a double peak shape due to the different travelling time of electrons and holes
- Compared pulse amplitude from experiment to simulation







- Produced a mesh containing several 150 µm square cells
- Signal columns were ganged together in lines along the Ydirection by surface electrode to mimic the metallization on the detector used in the experiment
- Graphitic columns modeled as perfect contacts on surface of column, with 2.5 µm radius
- Simulations performed at 25V



- Better understand results of test beam with a 3D Diamond detector using 120 GeV protons*
- Understand charge sharing between neighboring cells, particularly when a bias column was missing
- Understand difference in charge collection in broken cells
- Then applied simple finite charge lifetime model to implement measured 70 ns charge lifetime

*F. Bachmair et al. Nuclear Instruments and Methods in Physics Research Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 786:97 – 104, 2015.



- Simulated MIPs passing through the area of a quarter cell
- Divided the quarter cell into 15x15 µm squares, and simulated a MIP hit at the center of each square
- Able to plot the charge collected as function of position





 Order of magnitude difference between charge collection times in broken cells and intact cells due to large region with low field due to missing columns



Weighting Field

- Observed the generation of a bipolar signal in strips adjacent to the one with the hit due to the shape of the weighting field around the graphitic columns
- These signals integrate to zero due to charge conservation
 when no traps are present





- Introduce a simple charge trapping model to mimic a 70 ns charge lifetime, now some charge is trapped before reaching electrodes resulting in a residual signal in the neighboring cells
- Negative signals observed in regions of intact cells, but below noise level
- In broken cell significantly more trapping, hence region with significant negative signals induced in neighboring cells, centered in position of missing bias column

1500

1000

500

-500

-1000

-1500



- Overall observe that relatively uniform charge collection for intact cell, even with trapping
- In case of missing HV column, region centered around column with high negative signal, and lower overall signal, as observed



Diamonds at the Christie's

- The Christie's is a hospital that specializes in the treatment of cancer in Manchester
- Want to use 3D diamond for dosimetry in radiotherapy.
- Working in collaboration with the Christie hospital
- Goal to have detectors that allow real time, high resolution monitoring of dose received by patient



Diamonds at the Christie's



Future Plans

- Need to investigate radiation hardness of 3D Diamond, and study the effect of irradiation on the columns, sample has been irradiated; pre irradiation columns had diameter either 1.1µm or 1.4µm and respective resistances as low as ~2.5×10⁶Ω and ~1.8×10⁶Ω
- Once sample is available again, will be able to compare this to column resistance post irradiation
- More measurements will be carried out at the Christie's using detectors with a purposely designed geometry
- Investigate the effects of different electrode geometries (e.g. Hexagonal, rectangular etc.) both with new detectors and more simulations
- Study the effects of varying electrode shape (e.g. branching electrodes?)

Thanks for listening

Backup Slides

Semiconductor equations

Electron Continuity Equation:

$$\frac{\partial n}{\partial t} = \frac{1}{q} \nabla \cdot J_n + (G_n - R_n)$$

Hole Continuity Equation:

$$\frac{\partial p}{\partial t} = -\frac{1}{q} \nabla \cdot J_p + (G_p - R_p)$$

Poisson Equation:

$$\nabla \cdot E = \frac{\rho_s}{\varepsilon_s}$$

- J Current Density
- G Carrier Generation rate
- R Carrier Recombination rate
 - ρ_s Total space charge density
- ϵ_{s} Permittivity of semiconductor

Pernegger Values

•
$$\mu_{low_e} = 1714 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$$

• $\mu_{low_h} = 2064 \text{ cm}^2 \text{ V}^{-1} \text{ s}^{-1}$

•
$$v_{sat_e} = 9.6 \times 10^6 \text{ cm s}^{-1}$$

•
$$v_{sat_h} = 14.1 \times 10^6 \text{ cm s}^{-1}$$

H. Pernegger et al. Charge-carrier properties in synthetic single-crystal diamond measured with the transient-current technique. Journal of Applied Physics, 97(7):–, 2005.

Simulation

- Carried out some simulations of 3D
 Diamond detectors
- Wanted to investigate the effects of missing columns, and the production of a wrong sign signal pulse observed at a test beam

hNegativeChargePositionAllCells_grid



M. Pomorski, P. Bergonzo, D. Trompson, F. Bachmair, L. Baeni I. Haughton, D. Hits, H. Kagan, R. Kass, L. Li, B. Caylar, A. Oh Fabrication, characterization of a 3d diamond detector. 13th Vienna Conference on instrumentation - VCI 2013, 2 2013.



Total number of holes measured by right signal line (No Traps)





Total number of holes measured by right signal line (No Traps)







